

### **IN THE SPECIFICATION**

Please replace the paragraph starting at page 9, line 22 and ending at page 10, line 9 with the following:

-- Since the device layer including the etched well having suitable material deposited thereon is generally positioned over the weak bond region 3 of the multiple layered substrate 100, the device layer 110 may readily be removed from the support layer 120. For example, the strong bond regions 4 may be etched away by through etching (e.g., normal to the surface through the thickness of the device layer in the vicinity of the strong bond region), edge etching (parallel to the surface of the layers), ion implantation (preferably with suitable masking of the etched well and deposited material to form the nozzle, or by selective ion implantation), or other known techniques. Since the above techniques are generally performed at the strong bond regions 4 (shown in Figure 4) only, the etched well and material deposited in the weak bond regions 3 (shown in Figure 4) are easily released ~~from~~ from the substrate, as schematically shown in Figure 56, for example with a handler 150.--